



**Chip Dimensions: 775 x 343 microns**  
**Chip Thickness: 100 microns**

### Features:

- +30 dBm typical Output Power at 12 GHz
  - 9 dB typical Small Signal Gain at 12 GHz
  - 40% typical PAE at 12 GHz
  - 0.3 x 2400 Micron Refractory Metal/Gold Gate
  - Sorted into 40 mA Idss Bin Ranges
  - Excellent for High Power, and High Power Added Efficiency
  - Ideal for Commercial, Military, Hi-Rel Space Applications
- 📄 [Download MwT-11 SPARAM Files](#) (s2p format)

The MwT-11 is GaAs MESFET device whose nominal 0.3 micron gate length and 2400 microns gate width make it ideally suited for applications requiring high power up to 1 watt. The chip is produced using MwT's reliable metal systems and all devices from each wafer are screened to insure reliability. All chips are passivated using MwT's patented "Diamond-Like Carbon" process for increased durability.

### RF Specifications at Ta= 25 °C

SYMBOL	PARAMETERS & CONDITIONS	FREQ	UNITS	MIN	TYP
<b>OIP3</b>	Output IP3 with two tones Vds=6.0 V Ids=0.6xIDSS=300 mA		dBm		45
<b>P1dB</b>	Output Power at 1dB Compression Vds=6.0 V Ids=0.6xIDSS=300 mA	12 GHz	dBm	28.0	30.0
<b>SSG</b>	Small Signal Gain VDS=6.0 V Ids=0.6xIDSS=300 mA	12 GHz	dB	7.0	9.0
<b>PAE</b>	Power Added Efficiency at P1dB VDS=6.0 V Ids=0.6xIDSS=300 mA	12 GHz	%		40
<b>IDSS</b>	Recommended IDSS Range		mA		400-800

### DC Specifications at Ta= 25 °C

SYMBOL	PARAMETERS & CONDITIONS	UNITS	MIN	TYP	MAX
<b>IDSS</b>	Saturated Drain Current Vds=3.0 V Vgs=0.0 V	mA	240		920
<b>Gm</b>	Transconductance Vds=2.0 V Vgs=0.0 V	mS	290	380	
<b>Vp</b>	Pinch-off Voltage Vds=3.0 V Ids=16 mA	V		-2.5	-5.0
<b>BVGSO</b>	Gate-to-Source Breakdown Voltage Igs= -2.4 mA	V	-6.0	-12.0	
<b>BVGDO</b>	Gate-to-Drain Breakdown Voltage Igd= -2.4 mA	V	-8.0	-12.0	
<b>Rth</b>	Chip Thermal Resistance	C/W		28	

#### Bin Selection Guide

Bin	A	B	C	D
<b>Idss</b>	240-	360-	480-	720-
<b>Range</b>	360	480	720	840